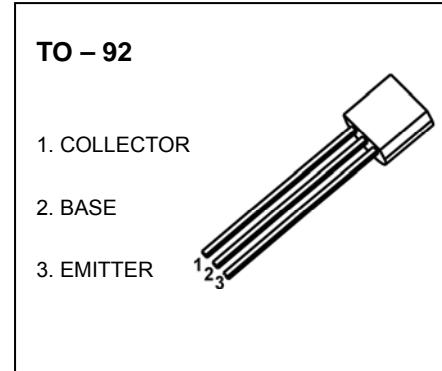


TO-92 Plastic-Encapsulate Transistors

BC546/BC547/BC548 TRANSISTOR (NPN)

FEATURES

- High Voltage
- Complement to BC556,BC557,BC558



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BC546	80
		BC547	50
		BC548	30
V_{CEO}	Collector-Emitter Voltage	BC546	65
		BC547	45
		BC548	30
V_{EBO}	Emitter-Base Voltage	6	V
I_c	Collector Current-Continuous	0.1	A
P_c	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BC546	V _{(BR)CBO}	I _C = 0.1mA, I _E =0	80		
	BC547			50		
	BC548			30		
Collector-emitter breakdown voltage	BC546	V _{(BR)CEO}	I _C =1mA, I _B =0	65		
	BC547			45		
	BC548			30		
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10µA, I _C =0	6			V
Collector cut-off current	BC546	I _{CBO}	V _{CB} =70V, I _E =0		0.1	µA
	BC547		V _{CB} =50V, I _E =0		0.1	µA
	BC548		V _{CB} =30V, I _E =0		0.1	µA
Collector cut-off current	BC546	I _{CEO}	V _{CE} =60V, I _B =0		0.1	µA
	BC547		V _{CE} =45V, I _B =0		0.1	µA
	BC548		V _{CE} =30V, I _B =0		0.1	µA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	µA
DC current gain	h _{FE} [*]	V _{CE} =5V, I _C =2mA	110		800	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =5mA			1.1	V
Base-emitter voltage	V _{BE}	V _{CE} =5V, I _C =2mA	0.58		0.7	V
		V _{CE} =5V, I _C =10mA			0.75	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			4.5	pF
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=100MHz	150			MHz

CLASSIFICATION of h_{FE}

RANK	A	B	C
RANGE	110-220	200-450	420-800